

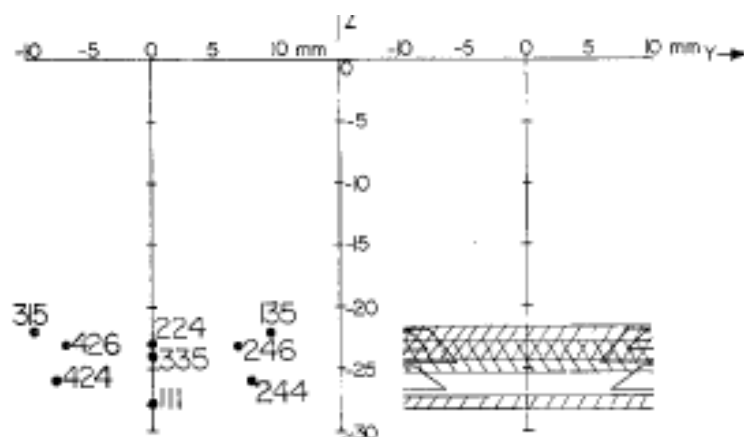
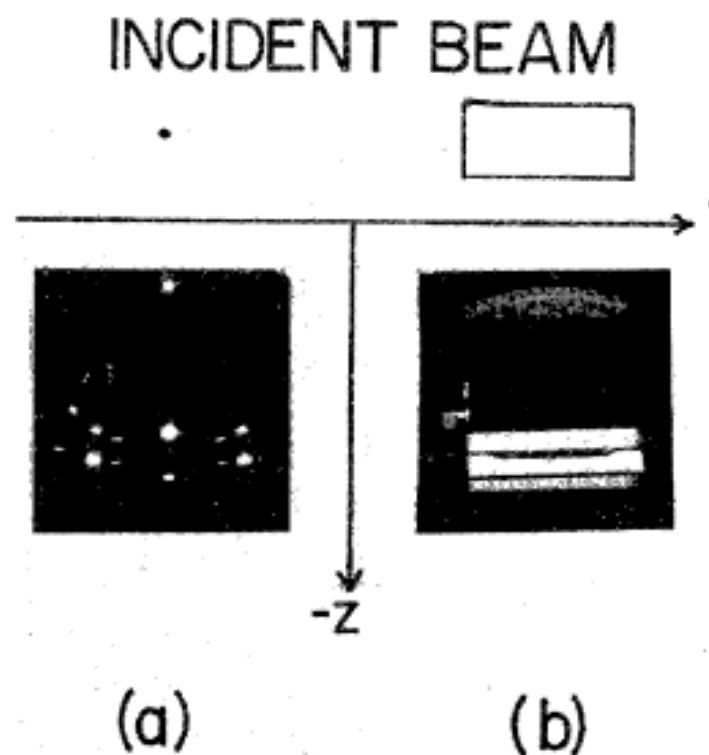
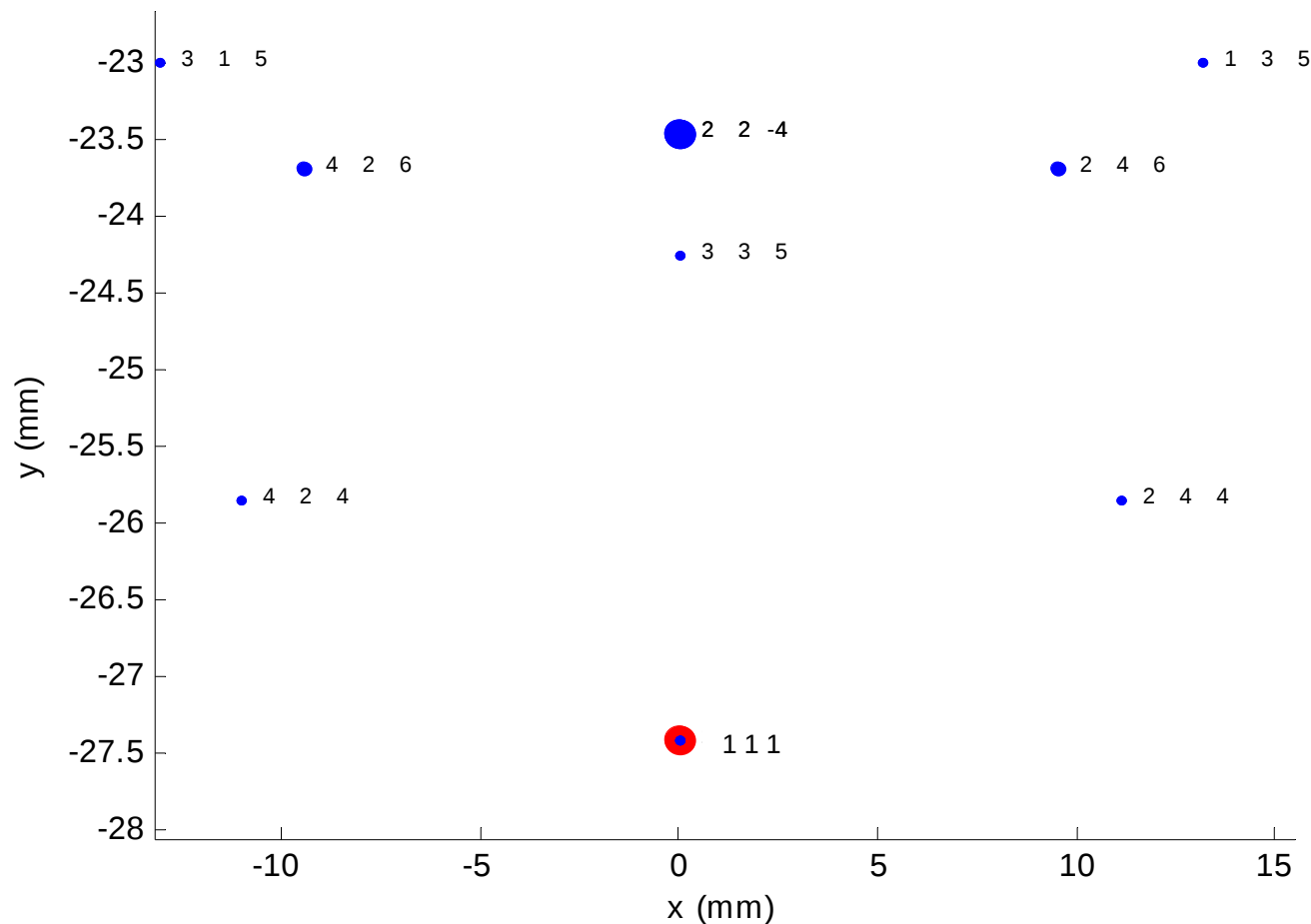


Fig. 4. Calculated position of identified reflections behind a doubly asymmetric Si 111 monochromator whose Bragg planes are at 30° to the xy plane and incident beam along negative x axis: (a) for a single polychromatic ray along the x axis, and (b) for a 10 mm high swath of parallel and polychromatic radiation.



Identification of "spurious" reflections in "channel cut" monochromators
 Vaclav O. Kostroun
 Nuclear Instruments and Methods 172 (1980) 243-247

Spurious reflections from $\bar{a}\bar{a}\bar{Si}(111)$ monochromator
 Gap -18 mm - $E = 3.954 \text{ keV}$ - $d = 3.1355 \text{ \AA}$



Matlab routine that generates the figures can be found at
http://www.cells.es/Beamlines/MSPD/Laue_spots_ccm

Simulated X-ray photograph 3 x 3 mm² After a Si(111) channel cut monochromator Gap = 3 mm

Spurious reflections from a Si(111) monochromator
 Gap 3 mm - E = 8.000 keV - d = 3.1355 Å

